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Charge Carrier Dynamics in Two-Dimensional Hybrid Perovskites: Dion-Jacobson vs. Ruddlesden-Popper Phases

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Abstract

Two-dimensional (2D) halide perovskites are promising materials for environmen-
tally stable next-generation optoelectronic device applications. Besides the widely in-
vestigated Ruddlesden-Popper (RP) phases, Dion-Jacobson (DJ) phases are attracting
considerable attention due to their rapid emergence as efficient solar cell materials.
However, there is very little atomistic understanding of the charge carrier dynamics
at ambient conditions for these DJ-phases, limiting the possibilities to tune their op-
toelectronic performances through compositional engineering routes. Here, by com-
bining nonadiabatic molecular dynamics with time-domain density functional theory
methods at room temperature, we compare the dominant non-radiative carrier recom-
bination and dephasing processes in RP and DJ monolayered lead halide perovskites.
Our systematic study demonstrates that performance-limiting nonradiative carrier re-
combination processes greatly depends on the electron-phonon interactions induced by
structural fluctuations, and instantaneous charge localization in these materials. The
stiffer interlayer packing due to the presence of single spacer dications, which separates
the lead iodide slabs, reduces the thermal fluctuations in the DJ-phase to a greater ex-
tent than that in the RP-phase 2D-perovskites. Specific electronic coupling between the
closely spaced lead iodide layers enhances delocalization of band-edge charge densities
in DJ-phase systems. Compared to the RP-phase, reduced inelastic electron-phonon
scattering in DJ-phase perovskites significantly limits intrinsic non-radiative recombi-
nation processes. Consequent enhancement in photogenerated charge carrier lifetime
makes DJ-phase perovskites potentially suitable for various optoelectronic devices. The
computational insights gained from this study allow us to outline a set of robust design
principles for DJ-phase perovskites to strategically tune their optoelectronic properties.

Introduction

Low-dimensional lead halide perovskites are promising candidates for a variety of stable op-
toelectronic devices such as solar cells,1–3 light-emitting diodes,4,5 photocatalysts,6–8 photo
and radiation detectors.9 Particularly, two-dimensional (2D) iodide perovskites attract sig-
nificant research interest due to their long-term stability at ambient conditions, significant
moisture resistance, rich chemical and structural diversity, and consequently widely tunable photovoltaic properties.\textsuperscript{4,5,10–13} In these materials, halide perovskite layers remain separated by long organic spacer cations (Fig. 1a-c) Among several 2D-halide perovskite structures, extensive studies of the Ruddlesden-Popper (RP) phases have demonstrated their possible applications in solar cells, color-pure photo-emitting diodes, X-rays, and photo-detectors.\textsuperscript{14–19} More recently, Dion-Jacobson (DJ) phases have emerged as another family of layered halide perovskites that exhibits promising efficiency in solar cell devices.\textsuperscript{20–27} The difference between these 2D-perovskites originates from the fact that a RP-phase contains two monocationic spacers whereas a DJ-phase contains only one dication spacer molecule per formula unit. Common chemical formulas of RP and DJ-phases are $A'^2A_{n-1}B_nX_{3n+1}$ and $A''A_{n-1}B_nX_{3n+1}$, respectively where $A'$ are monocations and $A''$ are dication-based spacer molecules. In these chemical formulas $A$ is smaller organic or inorganic cations (such as methylammonium or Cs), $B$ is divalent metal, and $X$ is halogen. The $B_nX_{3n+1}$ constructs the inorganic layer, containing corner-shared $BX_6$ octahedra, and spacer cations (i.e. $A'$ and $A''$) non-covalently hold these inorganic slabs. The thickness of the inorganic layer depends on the parameter $n$ that represents the number of $BX_6$ layers in each the $B_nX_{3n+1}$. In most of the RP and DJ-phases reported to date, the $B_nX_{3n+1}$ layer plays a central role in the basic optoelectronic properties such as band gap, carrier mobility, and optical absorption.\textsuperscript{20,22,28–30} The organic spacer cations do not directly participate electronically to the band edge characteristics, but influence the structural distortions in the $B_nX_{3n+1}$ layer and interlayer charge screening through image charge effect.\textsuperscript{31,32} These effects, when they are considered as static effects, already impact important properties such as optical band gap, exciton binding energy, carrier mobility in 2D halide perovskites. Recent in-depth studies further bring out more subtle roles of these spacer cations on determining the photo-physical properties of mechanically ‘soft’ 2D-perovskites at room-temperature.\textsuperscript{33–39} The geometry and chemical bonding in the inorganic sublattices and their non-covalent interactions with organic spacers, lead to substantial structural dynamics in these halide perovskites at ambient conditions. Strong and
complex dynamic coupling between the inorganic layer and the spacer cations significantly enhances the electron-phonon interactions, increasing the non-radiative charge recombination rates.\textsuperscript{38,40} In this recombination process, the electronic energy of photo-generated carriers gets rapidly transferred to the vibrational motions of the lattice, significantly deteriorating the performance of an optoelectronic device. Several approaches, such as including $\pi$-stacked spacer cations, increasing the thickness of the inorganic layers, and monovalent cation mixing have been investigated to try mitigating the non-radiative carrier losses in RP and also 3D halide perovskites.\textsuperscript{35–39} At the atomistic level, all these approaches result in an increase of the organic and inorganic sublattice stiffness. This weakens the electron-phonon coupling at room temperature, and consequently prolongs the photo-generated carrier lifetime. In the DJ-phase, the presence of a single dicationic spacer molecule provides unique opportunities to enhance the lattice stiffness by (1) introducing non-covalent interlayer halogen interactions between inorganic slabs and (2) by avoiding the floppiness of the organic barrier induced by the intermolecular van der Waals interactions in the spacer cation layer. These specific structural features should reduce the low-frequency structural fluctuations of the lattice, therefore weaken the thermally induced electron-phonon coupling, and result in a longer carrier lifetime. Furthermore, the non-covalent interlayer halogen interactions also promote increased electronic coupling between the layers and enhances the carrier delocalization.\textsuperscript{20,24,26} A recent time-resolved photoluminescence spectroscopy-based study has indeed reported that the average carrier lifetime for the DJ lead iodide perovskite is twice that of the RP-phase.\textsuperscript{27} The longer carrier lifetime underpins observed enhancement of the DJ perovskite-based planar heterojunction solar cells efficiency to $>17\%$. These promising preliminary reports demand a more in-depth atomistic investigation of the charge carrier dynamics the DJ-phase than has been done so far.\textsuperscript{25} The fundamental structure - optoelectronic property relationships suggest further guidelines for efficient low-dimensional photoactive materials design and discovery. Particularly, a wide variety of possible short-length diamine molecules may serve as organic spacers thus providing extensive compositional space for fine-tuning the photophys-
ical properties of these emerging layered perovskites.

Following our previous investigations of the dynamic structure-property relationships in low-dimensional and 3D-halide perovskites,\textsuperscript{15,16,41–43} the current work, combines \textit{ab initio} real-time time-dependent density functional theory (DFT) and non-adiabatic molecular dynamics (NAMD) modeling to systematically study the intrinsic and room temperature non-radiative charge carrier recombination in RP and DJ lead iodide perovskite phases. To underline the importance of spacer cations, we only consider single layer (n = 1) 2D-perovskites that does not contain 3D bulk-like slabs. It also allows addressing complex non-adiabatic carrier dynamics at a reasonable computational cost. Due to their well-characterized phase-pure synthesis, single layer 2D-perovskites have been investigated extensively to evaluate the fundamental structure-property relations.\textsuperscript{35,44–50} We consider RP-phase $A'_{2}\text{PbI}_4$ 2D-perovskites with two commonly explored cations, long alkyl chain n-butylammonium (BA) and benzene ring containing phenylethylammonium (PEA).\textsuperscript{15,29,51,52} A comparison between these systems reveals the effects of stacked aromatic ring spacer cations on the structural dynamics and charge carrier recombination processes. Among the experimentally synthesized DJ-phase perovskites, we chose the structurally well-characterized (aminomethyl)piperidinium (3AMP) based (3AMP)$\text{PbI}_4$ as the representative DJ system for our study.\textsuperscript{20} Restricted structural dynamics and charge delocalization through the $\text{PbI}_4$ interlayer stacking in (3AMP)$\text{PbI}_4$ significantly reduce the non-radiative recombinations of photo-generated free carriers, prolonging the carrier lifetime. Overall, we find better photophysical characteristics for DJ-phase perovskites compared to RP-phase ones. By exploring at the atomic scale the relationships between the structural and charge carrier dynamics, our study reveals the subtle effects of electron-phonon interactions on the recombination processes in photoactive 2D iodine perovskites. We emphasize the importance of spacer cation engineering strategies to improve the performances of layered perovskites-based optoelectronic devices.
Results and Discussion

Static Structural Properties

The optimized ground-state geometries of (BA)$_2$PbI$_4$, (PEA)$_2$PbI$_4$, and (3 AMP)PbI$_4$ shown in Fig. 1 demonstrate key differences that arise from the inorganic layer - spacer cations non-covalent interactions. In all systems, the single-layer PbI$_6$ octahedra exhibit corner-shared connectivity and has similar Pb-I bond lengths. However, due to the single and short spacer dication in (3 AMP)PbI$_4$, the PbI$_6$ octahedral slabs form interlayer van der Waals interactions that are completely absent in the investigated RP-phase perovskites (Fig. 1a-c). In (3 AMP)PbI$_4$ the interlayer axial I...I distances range from 4.13 Å to 4.21 Å, being well within the van der Waals diameter of iodine atoms ($\sim$ 4.44 Å).$^{20,53}$ These non-covalent interactions in (3 AMP)PbI$_4$ introduce interlayer coupling between perovskite slabs.$^{20}$ Moreover, the equatorial Pb-I-Pb angles differ where (3 AMP)PbI$_4$ has less overall distortion and more linear angles compared to (BA)$_2$PbI$_4$ and (PEA)$_2$PbI$_4$ (Fig. 1d-f). However, despite the denser packing of the organic barrier in the DJ-phase, all the structures have seemingly similar H$_3$N—I (equatorial) distances from a static viewpoint. This important aspect will be clarified from a dynamical viewpoint (vide infra).

Static Electronic Properties

We investigate the ground-state electronic structures of 2D-perovskites with the optimized structures obtained from DFT-based simulations (see Methods). When including spin-orbit coupling (SOC) corrections, the calculated electronic band gaps are 1.18 eV, 1.34 eV and 1.37 eV for (3 AMP)PbI$_4$, (BA)$_2$PbI$_4$ and (PEA)$_2$PbI$_4$, respectively. Except systematic and expected underestimation of electronic band gaps compared to the well documented experimental data, the PBE+SOC level of theory is a reliable approach to capture the electronic band gap trend of halide perovskites and their overall electronic structures.$^{31,42,54-56}$ The electronic band gap underestimation originates due to the absence of electronic many-body

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Figure 1: Optimized structures and electronic properties in 2D-perovskites. DFT-based optimized structures of (a) (BA)$_2$PbI$_4$, (b) (PEA)$_2$PbI$_4$ and (c) (3AMP)PbI$_4$. Colors: hydrogen (white), carbon (black), nitrogen (blue), iodine (pink), lead (grey). The dashed red lines and numbers show the average distances between the interlayer axial I atoms. (d-f) The equatorial Pb-I plane and Pb-I-Pb angles of the optimized structures as shown in (a-c). The deviation of Pb-I-Pb angles from linearity (i.e. 180°) characterizes the extent of PbI$_6$ octahedral distortion. The electronic charge densities of (g) VBM and (h) CBM for (3 AMP)PbI$_4$. The band edge charge densities are delocalized over the inorganic layer. The closely spaced axial I atoms form interlayer coupling in the VBM state. The electronic structures are calculated using PBE-GGA+SOC level of theory (see Methods). (i) Comparison of valence band dispersion curves along the stacking axis for these 2D-perovskites.
interactions which are prohibitively expensive to include in the simulations for such large structures.\textsuperscript{54,57,58} The band-edge charge densities and the projected density of states show that both the valence band maximum (VBM) and the conduction band minimum (CBM) are delocalized over the Pb-I framework, without any identifiable contributions from the organic spacer cations (Fig. 1g,h, S5).\textsuperscript{31,59} The VBM has contributions from the $\sigma$-antibonding overlap between the 5p-orbitals of I and 6s-orbitals of Pb (Fig. 1g, S5,S6). Whereas, the dominant contribution to the CBM is the Pb 6p-orbitals along with small contributions from I 5p-orbitals form $\sigma$-antibonding overlap (Fig. 1h, S5,S6). The details of orbital overlaps and bonding types at the band edges further illustrates the structure - optoelectronic property relationship in these 2D-perovskites. More linear equatorial Pb-I-Pb angle (that is close to 180°) enhances the $s$ - $p$ orbital overlap between Pb and I. Due to the anti-bonding nature of the VBM, such increased orbital overlap results in an up-shift in the valence band edge energy level. As discussed in previous studies, it mainly causes a reduction in the band gap for more linear PbI$_6$ octahedral connectivity.\textsuperscript{42,43,59–61} Thus, in general, the smaller the Pb-I-Pb angle distortion, the smaller the electronic band gap in halide perovskites. This structure-property relation explains most computed electronic band gap variations of the 2D-perovskites; as the average Pb-I-Pb equatorial angles reduce (3AMP)PbI$_4$ > (BA)$_2$PbI$_4$ > (PEA)$_2$PbI$_4$, the electronic band gap follows the opposite trend.\textsuperscript{60,61}

Additionally, the axial iodide atoms of consecutive perovskite layers in (3AMP)PbI$_4$ undergo non-covalent interactions as the I...I distances (4.13 - 4.21 Å) remain within their van der Waals diameter ($\approx$ 4.4 Å). Considering the charge density of the VBM as shown in Fig. 1g (3D) and in Fig. S7 (2D), the repulsive electrostatic interaction between the axial I-5p orbitals further destabilizes the valence band edge and shifts its energy level upward.\textsuperscript{20} The CBM state, however, remains mostly unaffected from these non-covalent interactions due to its in-plane charge density distribution (Fig. 1h). Therefore, the interlayer halogen interaction contributes to the red-shift of the band gap value of (3AMP)PbI$_4$. Due to the large lead iodide interlayer distances in RP-phase 2D-perovskites, the axial I...I pairs remain
spatially apart (> 8.5 Å), making the electronic coupling along the stacking axis and its effects on the electronic band gap negligible.

Figure 1i shows the band structures along the stacking direction (c-axis), \( \Gamma \rightarrow Z \), which emphasizes the dispersive nature of the valence band only for (3 AMP)PbI\(_4\). This further confirms the unique interlayer electronic coupling in the DJ-phase perovskite due to the shorter interlayer PbI distances. The VBM remains largely flat for (BA)\(_2\)PbI\(_4\) and (PEA)\(_2\)PbI\(_4\), depicting the lack of perovskite interlayer halogen interactions in these systems. VBM dispersion may be more favorable for interlayer hole-transport in the DJ-phase perovskites compared to RP-phase materials. However, the conduction band edges that have a dominant contribution of the non-bonding Pb-5p state, remain mostly alike in terms of band dispersion for all of the 2D-perovskites (see Fig. S8).

**Dynamic Structural Properties**

At finite temperature, structural dynamics significantly influences the instantaneous geometry and charge carrier dynamics in halide perovskites.\(^{35,44,62-64}\) Thus, we perform ab initio molecular dynamics (AIMD) simulations at 300 K to explore the dynamical behavior of these 2D-perovskites (see Methods).

We compute the root mean square fluctuations (RMSF) for individual inorganic sites and organic cations of 2D-perovskites to apprehend the overall extent of thermally induced fluctuations in these materials. As shown in Fig. 2, each individual component of (BA)\(_2\)PbI\(_4\) has the highest RMSF value, revealing that this BA-based perovskites has the largest structural fluctuations. Due to the \( \pi-\pi \) interactions enhancing the stiffness along the cations stacks, the thermal distortions of the perovskite and organic layers are considerably suppressed in (PEA)\(_2\)PbI\(_4\) compared to the long alkyl cation based (BA)\(_2\)PbI\(_4\).\(^{35}\) The dicationic spacers in (3 AMP)PbI\(_4\) removes the van der Waals gap in the spacer layer and the short dications allow for the formation of non-covalent halogen interactions between two neighboring perovskite slabs. This further restricts the thermal motions of Pb and 3AMP cations. As the
single perovskite layer in all of these 2D-perovskites are chemically identical, it is evident that the spacer cations are the origin of variations to the overall structural rigidity and dynamics under ambient conditions. Therefore, the choice of spacer cations is an effective tool to fine-tune the dynamical behavior of low-dimensional halide perovskites.

Figure 2: Influences of the spacer cations on the lattice thermal fluctuations for 2D-perovskites. The root means square fluctuations for Pb, I, and organic spacers at 300 K for DJ- and RP-phase perovskites.

The dynamical structural study shows a sizable difference in RMSF between DJ and RP-phases, which already indicates the importance of the mechanical coupling between the inorganic lattice and the cations in the barrier. Closer inspection reveals that differences in the equatorial Pb-I-Pb bond angle fluctuations in these 2D-perovskites, can be attributed to the steric interaction with spacer cations. The intrusion depth of the NH$_3$ group into the open grooves of perovskite layers produces steric effects exerted by the spacer cations on the inorganic layer, which is distinct for DJ and RP-phases. From the viewpoint of the inorganic layer, the most striking difference between the three systems is related to the equatorial Pb-I-Pb bond angle thermal distributions (Fig. 3a). (3AMP)PbI$_4$ exhibits a skewed distribution with a Pb-I-Pb mode angle (that is the most frequent angle) at 162.4° (Fig. 3a). The RP-phases PEA and BA cation-based perovskites have a Gaussian-type distribution around a more distorted average structure with mode angles at 148.4° and 151.8°, respectively. It is
well known that such distortions deeply affect the electronic structure of 2D-perovskites.\textsuperscript{59,60} From the viewpoint of the organic spacers, differences between DJ and RP-phases are also revealed by the dynamical study. The distances between the equatorial iodide atoms and the nitrogen atom of the NH\textsubscript{3} group in the spacer cations reveal the fluctuations of the intrusion depth (Fig. S1a,b). As shown in Fig. 3b, the time averaged distances point to shorter N...I lengths in (3 AMP)PbI\textsubscript{4} compared to the monocationic RP-phase perovskites. Short N...I lengths are consistent with deeper intrusion depth and reduced spatial separation between the spacer and inorganic frame, imposing steric constraints on the Pb-I equatorial plane of PbI\textsubscript{6} octahedra. In response to this steric crowding in the (3 AMP)PbI\textsubscript{4}, the equatorial inorganic plane expands, making the average Pb-I-Pb angles relatively linear and increasing instantaneous angle values compared to the RP-phase 2D-perovskites (Fig. 3a). The increased average equatorial Pb-Pb distance in 3AMP-based perovskites also supports the spacer cation induced in-plane expansion of its perovskite layers (see Fig. S2 for details). The Pb-I bond length dynamics exhibit similar distributions for all three 2D-perovskites as detailed in the Supporting Information (SI), Section S1.

To further analyze the dynamical interactions between the inorganic and organic sublattices, we calculate the distances between the H atoms of the NH\textsubscript{3} group in the spacer and the iodide of the Pb-I equatorial plane (Fig. S4). As demonstrated in previous studies, these non-covalent interactions form hydrogen bonds between the inorganic and organic sublattices, influencing their coupled thermal motions at finite temperatures.\textsuperscript{41,42,65,66} In Fig. 3c, the N-H...I distance in the DJ-phase is more narrowly distributed compared to that in the RP-phase perovskites. Narrow distribution of this non-covalent bond suggests consistent dynamical coupling between perovskite layer and spacer cations in (3 AMP)PbI\textsubscript{4}.\textsuperscript{42,43} Furthermore, the ensemble average of N-H...I is shorter for DJ-phase (3.9 Å) compared to RP-phase perovskites (≈ 4.3 Å). At a qualitative level, considering the dominant electrostatic nature of this non-covalent interaction, the shorter average N-H...I distance indicates the stronger hydrogen bonding interactions in (3 AMP)PbI\textsubscript{4}.\textsuperscript{67} Such hydrogen-bond forma-
Figure 3: Structural dynamics at 300 K in 2D-perovskites. (a) The histograms of equatorial Pb-I-Pb bond angles computed over AIMD simulation trajectories of all three 2D-perovskites. (b) The mean distances between in-plane I of inorganic equatorial plane and N atoms of NH$_3$ group of spacer cations. The histograms of (c) the distances between in-plane I and H atoms of NH$_3$ of spacer cations and (d) the axial I...I distances between two stacked inorganic layers. We fit the distributions with the beta distribution function as plotted in solid line.

Another structural feature unique to the DJ-phase perovskites, are the short interlayer distances between inorganic layers. Shown in Fig. 3d, the axial iodine atoms maintain short interlayer I...I distances ($\approx 3.2$ - $5.0$ Å) throughout the AIMD trajectory. These reduced instantaneous I...I distances indicate a strong dynamical interlayer coupling between the in-
organic layers in \((3\text{AMP})\text{PbI}_4\). Due to the significantly larger interlayer spacing between inorganic layers, structural fluctuations do not induce fluctuations of the interlayer electronic coupling in RP-phase 2D-perovskites (Fig. 3d). As discussed later, the presence of the interlayer electronic coupling influences the optoelectronics of DJ-phase 2D-perovskites to a noticeable extent. It is worth mentioning that as we perform AIMD with constant experimental cell parameters, volume relaxation induced structural fluctuations are not included in the simulations. However, we expect similar overall structural dynamics even after considering such fluctuations in these 2D-perovskites.\(^{71}\)

**Adiabatic Fluctuations of the Electronic Properties**

To explore the direct influence of finite-temperature structural dynamics on the optoelectronic properties of 2D-perovskites, we next plot the electronic band gap distribution calculated along the AIMD trajectories (Fig. 4a). As shown in the histograms, \((3\text{AMP})\text{PbI}_4\) exhibits the most narrowly distributed and distinctly red-shifted band gaps over time among all the 2D-perovskites considered here. The average and standard deviations of the electronic band gap distributions for all 2D-perovskites are listed in Table 1. These distributions demonstrate that the equatorial Pb-I-Pb bond angle is the dominant descriptor affecting instantaneous electronic band gap of both RP and DJ-phase 2D-perovskites. As Pb-I-Pb angles in \((3\text{AMP})\text{PbI}_4\) skew towards higher values \(\approx 162^\circ\), the \(\text{PbI}_6\) octahedra are less distorted in this perovskite (Fig. 3a), red-shifting its electronic band gap distribution. Furthermore, considering two RP-phase perovskites, narrower Pb-I-Pb angle distribution of \((\text{PEA})_2\text{PbI}_4\) results in less dispersed band gap values than that in \((\text{BA})_2\text{PbI}_4\).

To demonstrate the robustness of the observed electronic band gap distributions in terms of applied computational methods, we further incorporate SOC corrections for evaluating the instant electronic band gaps along the simulated trajectories. The SOC effect substantially alters the band edge electronic properties in halide perovskites.\(^{31,54,58,72}\) To off set the numerical cost due to inclusion of SOC, we consider hundreds of instant structures, equally
Figure 4: Dynamic electronic structures in 2D-perovskites. (a) The histogram distribution of PBE band gaps along the AIMD trajectories for 2D-perovskites. The DJ-phase perovskite exhibits narrowly distributed and red-shifted band gaps at room-temperature. The distribution characters remain unchanged with the inclusion of SOC corrections as shown in Fig. S9. (b) The thermal broadening in the VBM and CBM states of \((BA)_2\)PbI\(_4\), \((PEA)_2\)PbI\(_4\), and \((3\text{AMP})\)PbI\(_4\). Both the VBM and CBM are narrowly distributed for DJ-phase perovskites, indicating a lesser thermal broadening of their band edge states. All band edge energies of a particular system are scaled to their average of VBM state energy. Solid lines are fitted with the beta-function to the distributions of data.

Spaced in simulation time for band gap evaluation. As we have discussed, incorporation of SOC corrections in absence of many-body electronic effects underestimates the band gaps by \(\approx 1\text{ eV}^{42,73}\). Figure S8 shows that the characteristics of the electronic band gap distributions obtained with SOC corrections closely resembles those calculated with plain PBE-GGA. Thus, the computationally cheap semi-local functionals can reasonably capture the qualitative nature of band gap fluctuations in 2D-perovskites that are dominantly influenced by the structural dynamics at ambient conditions.

To understand the impact of structural fluctuations on the individual band-edge states, we compute the relative position of VBM and CBM energy states over the simulation time. In Fig. 4b, both the VBM and CBM exhibit narrower distributions for \((3\text{AMP})\)PbI\(_4\) compared to \((BA)_2\)PbI\(_4\) and \((PEA)_2\)PbI\(_4\) (Table S1, SI). While the distribution in the VBM energy state mainly originates from the fluctuations in the equatorial Pb-I-Pb angles, the displacement in Pb sites dominantly controls the instant relative position of the CBM state. Skewed
and narrower distribution of Pb-I-Pb angles (Fig. 3a) and smaller RMSF of Pb atoms (Fig. 2) in DJ-phase perovskite leads to their sharper band edges compared to RP-phase perovskites. Narrow distributions of both band edges consequently contribute to reduced band gap fluctuations in (3AMP)PbI$_4$ as we find in Fig. 4a.

**Importance of Non-adiabaticity for Non-radiative Recombinations**

The finite-temperature induced structural distortions play a decisive role in photo-generated charge carrier dynamics in low-dimensional halide perovskites.$^{38,40}$ We employ non-adiabatic molecular dynamics (NAMD) with real-time time-domain DFT to investigate the comparative impact of structural dynamics on the non-radiative carrier recombination rate in RP- and DJ-phases of lead iodide perovskites. As shown in Fig. 5a, the evolution of carrier populations with time depicts a much faster rate of photo-generated charge recombination in (BA)$_2$PbI$_4$ compared to both (3AMP)PbI$_4$ and (PEA)$_2$PbI$_4$. Using the short-time linear approximation of the exponentially increasing function (discussed in Methods$^{38,74}$) we find that the non-radiative carrier life-times are 4.9 ns, 14.5 ns, and 79.7 ns for (BA)$_2$PbI$_4$, (PEA)$_2$PbI$_4$, and (3AMP)PbI$_4$, respectively (Table 1). The overall trend and longer carrier lifetime of the DJ-phase lead iodide perovskites is consistent with recent experimental reports.$^{24,27,75}$ Moreover, estimated carrier lifetimes for all the 2D-perovskites are on the nanosecond time scale, matching reasonably well with the time-scale of respective experimental values.$^{24,27,47,76}$ Thus, our study unambiguously demonstrates that the spacer molecules have an important influence on the charge carrier recombination dynamics in 2D-halide perovskites. The additional influence of interlayer electronic coupling related to iodine atoms will be demonstrated in the next part.

The dynamic coupling between the electronic and lattice degrees of freedom affects the non-radiative charge relaxation and recombination processes that directly impact the performance of perovskite-based optoelectronic devices.$^{38,74,77,78}$ As key factors such as electron-phonon interactions and energy gaps dominantly influence the non-radiative carrier recom-
Table 1: The PBE+SOC (PBE-GGA) calculated electronic band gaps, average and standard deviation (stdv) of PBE band gap values along AIMD trajectories, nonradiative carrier recombination times, pure-dephasing time for \((\text{BA})_2\text{PbI}_4\), \((\text{PEA})_2\text{PbI}_4\) and \((3\text{AMP})\text{PbI}_4\).

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combination, we further investigate these aspects in details.

The electron-phonon interactions at finite temperature involve both elastic and inelastic carrier scattering in the hybrid materials.\(^{38,74,79,80}\) At ambient conditions, an energy exchange between electronic and vibrational subsystems occurs through the inelastic scattering mechanism. In this process, during non radiative recombination, the extra energy that is generated from the recombined charges, is dissipated to the nuclear degrees of freedom.\(^81\) To quantify the strength of this scattering process, the non-adiabatic coupling (NAC) constants have been calculated along the simulated trajectories.\(^82,83\) Physically, a higher value of the NAC signifies a stronger coupling between electrical and lattices degrees of freedom underpinning inelastic scattering processes and consequently indicating faster charge recombination in a material.\(^84–86\) Note that, the intra-band charge relaxation rates in the valence and conduction bands are much faster than the inter-band relaxation across the electronic band gap.\(^36,37\)

Thus, we reasonably approximate that the NAC strengths between the VBM and CBM is representative of the limiting inelastic process for the non-radiative recombinations. In Fig. 5b, the histograms of the instantaneous NAC values demonstrate frequent occurrences of strong VBM-CBM non-adiabatic coupling in \((\text{BA})_2\text{PbI}_4\) and \((\text{PEA})_2\text{PbI}_4\) along their MD trajectories. The instantaneous NACs have been calculated for each time step of the AIMD trajectory. The frequent occurrences of high instantaneous NAC values in the RP-phase perovskite indicate frequent opening of non-adiabatic channels by which photo-generated electrons and holes undergo non-radiative recombinations. Over the simulation time, it results in a faster increase of the recombined carrier population in the valence band edge of the RP-phase perovskite compared to the DJ-phase one.
Figure 5: The nonradiative carrier recombination and nonadiabatic coupling (NAC) in 2D-perovskites. (a) The recombined electron-hole population in (BA)$_2$PbI$_4$, (PEA)$_2$PbI$_4$, and (3 AMP)PbI$_4$ over time. We fit the time-dependent population increase to $f(t) = 1 - \exp (-t/\tau)$ where $\tau$ is the electron-hole recombination time. (BA)$_2$PbI$_4$ and (3 AMP)PbI$_4$ have the fastest and the slowest recombination rates, respectively. (b) The histogram distribution of absolute instantaneous NAC values with magnitude >0.0015 eV. Plotted NACs are calculated between VBM and CBM states for 2D-perovskites. (BA)$_2$PbI$_4$ and (PEA)$_2$PbI$_4$ reveal more occurrences of high instantaneous NAC values over the simulation time. A histogram with a complete range of NAC values has been included in the SI. The instant (c) VBM and (d) CBM charge densities for the time steps where the NAC is highest (0.0084 eV) in (BA)$_2$PbI$_4$. Both the band edges are closely localized, enhancing the overlap between the states. The instant (e) VBM and (f) CBM charge densities of (3 AMP)PbI$_4$ at the snapshot of time with the highest NAC (0.0056 eV). The delocalized VBM along the stacking direction is prominent and partially reduces the orbital overlap between band edge states.
To understand the origin of different NAC strengths in the studied 2D-perovskites, we closely examine \((\text{BA})_2\text{PbI}_4\) and \((3\text{AMP})\text{PbI}_4\) that exhibit the fastest and slowest recombination rates, respectively. The wavefunction overlap between two participating states at sequential time-steps and phonon velocities gives rise to finite instantaneous NAC values.\(^{83}\) The stronger the wavefunction overlap and the higher the phonon velocity, the larger the NAC value. Here, we are focused on the electron-hole recombination across the band gap where the dominant participating states are the VBM and CBM. As both the VBM and CBM states are confined to the inorganic frame (Fig. 4a), the thermal fluctuations in the Pb and I sites lead to fluctuations of the overlap between the wavefunctions and are therefore indicative of the magnitude of the NACs. Thus, higher structural fluctuations in Pb-I sites in \((\text{BA})_2\text{PbI}_4\) underpin the frequent occurrence of higher NAC values in this 2D-perovskite compared to the DJ-phase systems. We further examine the charge densities of band-edge states for snapshots in time corresponding to the high instantaneous NAC values. As shown in Fig. 5c,d for \((\text{BA})_2\text{PbI}_4\), both the VBM and CBM instantaneous charge densities are localized over closely spaced regions of the Pb-I framework. These produce finite wavefunction overlap, resulting in the strong non-adiabatic coupling between the band edge states. However, in the case of \((3\text{AMP})\text{PbI}_4\) the band-edge charge densities are delocalized, indicating a weaker overlap between the VBM and CBM states (Fig. 5e,f). The VBM state, in particular, shows extended one-dimensional charge delocalization through the axial I atoms that form interlayer stacking in the DJ-phase perovskite Fig. 5e. Undoubtedly, the short distances between these axial I atoms open up unique channels for extended charge delocalization in the VBM. Moreover, as the AIMD simulation depicts in Fig. 3d, the close I...I stacking remains intact throughout the trajectory at 300 K, demonstrating continued extended charge delocalization for the valence edge of DJ-phase perovskites. Due to possible SOC effects on the charge distributions in lead halide perovskites, we also calculate the instantaneous band edge electronic properties with PBE+SOC level of theory. As we find in Fig. S10, the overall nature of instant VBM and CBM charge distributions in RP- and DJ-phase perovskites
remain unchanged in the presence of SOC corrections, demonstrating the robustness of our main conclusions irrespective of the computational methods employed. Thus, both the delocalized band-edge charge densities and reduced structural fluctuations in (3 AMP)PbI₄ give rise to smaller NAC values compared to that of (BA)₂PbI₄. Partial suppression of NAC-induced electron-hole non-radiative recombination helps to enhance the carrier lifetime for the DJ-phase 2D-perovskite as shown in Fig. 5a. Due to π stacking, the thermal fluctuations and consequently instantaneous NACs are relatively weaker in (PEA)₂PbI₄ compared to alkyl spacer-based (BA)₂PbI₄. This explains slower electron-hole recombination rate of PEA-based perovskite.

The molecular dynamics study gave us the first indication on the atomistic origin of the mechanical coupling between the perovskite layer and the cation. To further understand the electron-phonon interactions that originate from complex structural dynamics, we calculate the influence spectra for RP- and DJ-phase 2D-perovskites. Such spectra are obtained by computing the Fourier transform (FT) of the unnormalized autocorrelation function (ACF) of the electronic band gaps over the simulation time. The influence spectra identify the particular phonon modes that are coupled to the electronic subsystem, and actively involved in the electron-hole non-radiative recombination processes. For the studied 2D-perovskites, all major peaks in the influence spectra emerge below 400 cm⁻¹ (Fig. 6). Therefore, the active phonon modes that encompass the nonradiative carrier relaxation, are low-frequency vibrational modes. Several 2D- and 3D-halide perovskites exhibit similar characteristics of influence spectra as are already reported by other studies. Despite the presence of C-H and N-H bonds in spacer cations with high-frequency vibrational modes (> 3000 cm⁻¹), only low-frequency modes appear in the spectra. As the band-edges consist of contributions only from the inorganic lead iodide frame (Fig. 4a,b), these high-frequency molecular modes remain absent in the carrier recombination across the band gap. The dominant low-frequency peaks in the range of < 150 cm⁻¹ can be assigned to the bending and stretching modes of the Pb-I frame for all 2D-perovskites (Fig. S11). The chemically identical inorganic
frame for all perovskites results in mostly similar peak positions in the spectra. The higher frequency peaks originate from the complex coupled dynamics of inorganic and spacer cation sublattices as detailed in the SI (Section S3). Interestingly, the most important contributions to the electron-phonon interactions (Fig. 6) correspond to the low frequency part of the 2D perovskites phonon spectrum (Figure S10), which includes basically only the lowest frequency cation vibrational mode (Figure S11). Therefore, the mechanical coupling between the spacer cations and the perovskite layer also strongly rely on the cations librational modes. A similar conclusion was drawn in ref.38 where the difference of the electron dynamics between n=1 and n=3 multilayered compounds was attributed to the additional contribution coming from the fast motion of the methylammonium cations, within the cage of the n=3 perovskite lattice.

![Figure 6: The electron-phonon interactions in 2D lead iodide perovskites. The fourier transform of autocorrelation for the band gap fluctuations in (BA)$_2$PbI$_4$, (PEA)$_2$PbI$_4$, and (3 AMP)PbI$_4$. The y-axis scale is arbitrary but in consistent units.](image)

Partially suppressed structural fluctuations, and the consequent narrowing of the electronic band gap distribution over time, therefore substantially reduces the electron-phonon coupling strengths in the DJ-phase perovskites. Thus, the analysis of the influence spectra strongly suggests that the enhanced stiffness induced by the stronger mechanical coupling
in the (3AMP)PbI\textsubscript{4} perovskite slows down the nonradiative carrier recombination processes by weakening the electron-phonon interactions at room temperature.

The NAC between two energy-states form a wavefunction superposition that further invokes the quantum transition between these states. The elastic electron-phonon scattering destroys the quantum coherence facilitating this process, leading to a loss of the superposition and consequently collapsing the wavefunction to only one of the states.\textsuperscript{81} Here, a rapid quantum decoherence over time suppresses the transition probability, enhancing the lifetime of a particular quantum state. Considering the electron-phonon recombination at semiconductor band edges, the faster the decoherence between VBM and CBM, the longer the expected recombination time. The typical timescale of quantum decoherence in solids lasts tens of femtoseconds (fs), much faster than the inelastic electron-phonon scattering induced processes. As detailed in the SI (Section S4), the calculated pure-dephasing time for all the investigated 2D-perovskites are in the range of 4.8 - 5.7 fs (Table 1). Due to the very similar pure-decoherence times of RP and DJ-phase perovskites, we conclude that the elastic scattering is not a decisive factor that can explain the distinctly different non-radiative carrier recombination rates of these materials (Fig. 5a).

Finally, we emphasize that observed physical processes that dominate non-radiative carrier recombination rates in different 2D iodide perovskites are non-intuitive. For a particular pair of states, Fermi’s Golden rule depicts that the recombination rate is inversely proportional to their energy band gap and is proportional to the square of the NAC value.\textsuperscript{89,90} Thus, marginally smaller average electronic band gap of (3 AMP)PbI\textsubscript{4} compared to RP-phase perovskite should result in a slightly shorter recombination time. However, much larger instantaneous NAC values in (BA)\textsubscript{2}PbI\textsubscript{4} and (PEA)\textsubscript{2}PbI\textsubscript{4} as shown in Fig. 5b, causes faster electron-hole recombination in these perovskites. Thus, it is apparent that the instantaneous spikes of the non-adiabatic couplings dominantly determine the non-radiative recombination rate of 2D lead-halide perovskites.

We also note that shorter N-H...I distance in the DJ-phase (Fig. 3c) can help to partially
suppress the electron-phonon interactions and polaron coupling strengths as demonstrated for the 3D-halide perovskites.\textsuperscript{91}

**Conclusion**

In conclusion, we investigate the room temperature charge carrier dynamics in representative structures of RP and DJ 2D-perovskites by combining time-domain DFT and NAMD simulations. Our calculations identify the dominant roles of finite-temperature structural fluctuations on the photo-generated carrier lifetime in these materials. The single dicationic spacer molecules in the DJ-phase (3AMP)PbI\textsubscript{4} removes the van der Waals gaps present between the two monocationic spacers in the RP-phase halide perovskites. This, in turn, compacts the spacer cation-inorganic layer stacking, and partially suppresses the structural dynamics in the Pb-I layers of (3AMP)PbI\textsubscript{4} at ambient conditions. The reduced equatorial Pb-I-Pb angle distortion and thermal fluctuations in (3AMP)PbI\textsubscript{4} lead to narrowly distributed red-shifted band gaps compared to the RP-phase perovskites. Instantaneous charge localization in (BA)\textsubscript{2}PbI\textsubscript{4} and (PEA)\textsubscript{2}PbI\textsubscript{4} results in the frequent opening of the non-adiabatic channels through which photo-generated carriers recombine non-radiatively. In contrast, halogen-halogen electronic coupling between the PbI layers partially helps the DJ-phase valence band charge densities to delocalize along the stacking axis, hindering the carrier recombination process. The longer carrier lifetime for (3AMP)PbI\textsubscript{4} suggests its superior performance over the more widely studied RP-phase perovskites for a range of optoelectronic applications.

This work provides a fundamental understanding of chemical and physical characteristics of the spacer cations to tune the optoelectronic performances of emerging types of lead halide 2D-perovskites. Replacing monocationic spacer cations with dicationic candidates likely not only suppresses the temperature-induced structural fluctuations but also introduces halogen interactions between the inorganic layers. Consequently, weaker electron-phonon interactions
and enhanced charge delocalization across the non-bonded perovskite layers substantially improves the charge carrier dynamics. Detailed knowledge of the dynamic structure - opto-electronic property relationships in these low-dimensional halide perovskites suggests several exciting strategies to enhance the electronic functionalities of these materials. For example, incorporation of short aromatic ring-based spacer molecules or more electrostatically active functional groups are some of the approaches that can increase the stacking strength between the dication spacer molecules and inorganic layers, beneficial for charge carrier dynamics.  

**Methods**

The density functional theory (DFT) calculations and *ab initio* molecular dynamics (AIMD) simulations have been performed using Vienna Ab Initio Simulation Package (VASP). The projected augmented wave (PAW) method within a plane-wave basis set with a cut-off energy of 500 eV has been adopted for all static DFT-calculations. We use the generalized gradient approximation (GGA) with the Perdew-Burke-Ernzerhof functional (PBE) form to approximate the exchange and correlation interactions. We construct the supercell with four formula units of \((BA)_2\text{PbI}_4\) and \((PEA)_2\text{PbI}_4\), and eight formula units of \((3\text{AMP})\text{PbI}_4\) and relax all the interatomic forces to less than 0.01 eV Å\(^{-1}\) during internal structural optimization. We further use the DFT-D3 method as described by Grimme and a 6×6×1 Γ-centered Monkhorst-Pack mesh for all the 2D-perovskites. To calculate more accurate electronic structures, spin-orbit coupling (SOC) was further applied self-consistently as implemented in VASP.

To investigate the charge carrier dynamics, we apply the mixed quantum-classical NAMD simulations with the decoherence-induced surface hopping (DISH) technique. In this method the electrons and nuclei are considered as quantum mechanical and semiclassical entities, respectively. Some of us and others have previously used this computational approach to compute the excited-state dynamics of inorganic and hybrid perovskites.
In AIMD simulations we use a $2 \times 2 \times 1$ Monkhorst-Pack k-point mesh, a time step of 1 fs and plane-wave energy cutoff of 400 eV. During AIMD calculations we considered PBE-GGA exchange-correlation functions and DFT-D3 corrections. The 0 K DFT optimized structures are considered as the initial structure for AIMD simulations and heated to 300 K using repeated velocity rescaling for 4 ps. Another 4 ps trajectories were generated using the canonical ensemble to ensure the thermal equilibrium of these systems. Following that, we generate 10 ps trajectories in the microcanonical ensemble and used 4 ps of these trajectories for the nonadiabatic coupling simulations. Note that, as we perform AIMD simulations by keeping the cell parameters to their experimental values at room temperature, present trajectories do not include effects of volume relaxation. However, as we consider the experimental cell parameters of ambient conditions for performing our AIMD simulations, volume relaxation will not affects the main conclusions of the study. We take into account all 4000 geometries along the AIMD trajectories and 1000 stochastic realizations of the DISH process for each geometry to compute the electron-hole recombination as implemented in the PYXAID code. We further evaluate the pure-dephasing time as considered in the optical-response theory for evaluating the decoherence time for these materials. Though recent work emphasizes the importance of SOC in nonradiative charge recombination, we have excluded this effect in our simulations as such computation significantly increases the computational cost. Another strong approximation is disregard of the excitonic effects that are present in all 2D halide perovskites. Proper incorporation of these effects requires time-dependent Bethe-Salpeter theory for dynamic lattices, an active current area of research. However, due to the fundamental methodological complexities such approaches are not completely developed and numerically feasible yet. We include more details on our computational methods in Section S5 of the SI file.
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Supporting Information Available

Electronic Supplementary Information (ESI) available: details of (BA)$_2$PbBr$_4$ and (PEA)$_2$PbBr$_4$ structures, charge carrier dynamics in these perovskites, fitting of carrier recombination functions.

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